



PJW7N04-AU

40V N-Channel Enhancement Mode MOSFET

Voltage	40 V	Current	6.5 A
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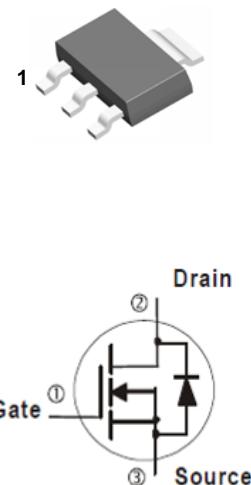
Features

- $R_{DS(ON)}$, $V_{GS} @ 10V$, $I_D @ 5A < 42m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ 4.5V$, $I_D @ 4A < 51m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams

SOT-223



Maximum Ratings and Thermal Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^(Note 4)	I_D	6.5	A
$T_A = 70^\circ C$		5	
Pulsed Drain Current ^(Note 1)	I_{DM}	26	
Power Dissipation	P_D	3.7	W
$T_A = 70^\circ C$		2.6	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~175	$^\circ C$
Typical Thermal Resistance - Junction to Ambient ^(Note 4,5)	$R_{\theta JA}$	40.3	$^\circ C/W$

- Limited only by Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	40	-	-	V
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.5	2.5	
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=5\text{A}$	-	35	42	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=4\text{A}$	-	44	51	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic <small>(Note 6)</small>						
Total Gate Charge	Q_g	$V_{\text{DS}}=20\text{V}, I_{\text{D}}=4.3\text{A}, V_{\text{GS}}=4.5\text{V}$ <small>(Note 1,2)</small>	-	4.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.4	-	
Gate-Drain Charge	Q_{gd}		-	1.8	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHZ}$	-	410	-	pF
Output Capacitance	C_{oss}		-	50	-	
Reverse Transfer Capacitance	C_{rss}		-	30	-	
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=20\text{V}, I_{\text{D}}=3.5\text{A}, V_{\text{GS}}=10\text{V}, R_{\text{G}}=1\Omega$ <small>(Note 1,2)</small>	-	4	-	ns
Turn-On Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	15	-	
Turn-Off Fall Time	t_f		-	8	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	6.5	A
Diode Forward Voltage	V_{SD}	$I_s=1\text{A}, V_{\text{GS}}=0\text{V}$	-	0.78	1.2	V

NOTES :

1. Pulse width $\leq 300\text{us}$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{\text{J(MAX)}}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_{\text{J}}=25^\circ\text{C}$.
4. The maximum current rating is package limited.
5. $R_{\theta\text{JA}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

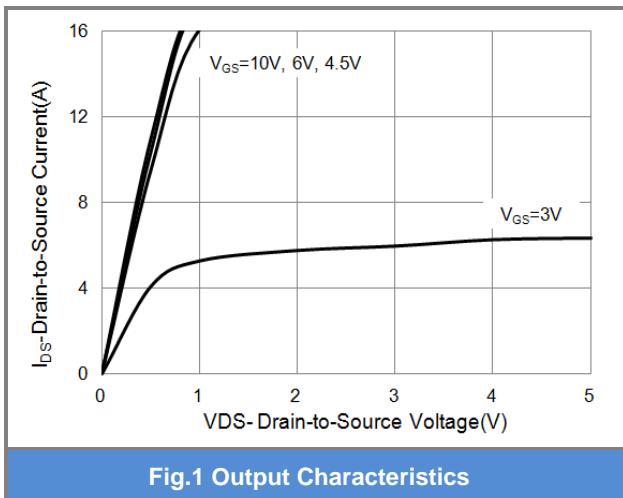


Fig.1 Output Characteristics

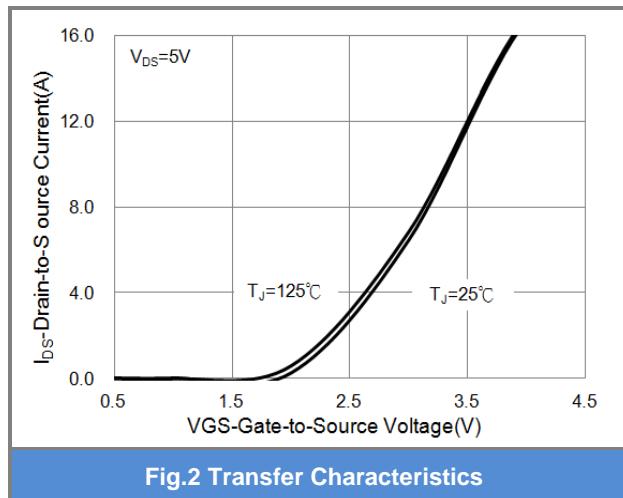


Fig.2 Transfer Characteristics

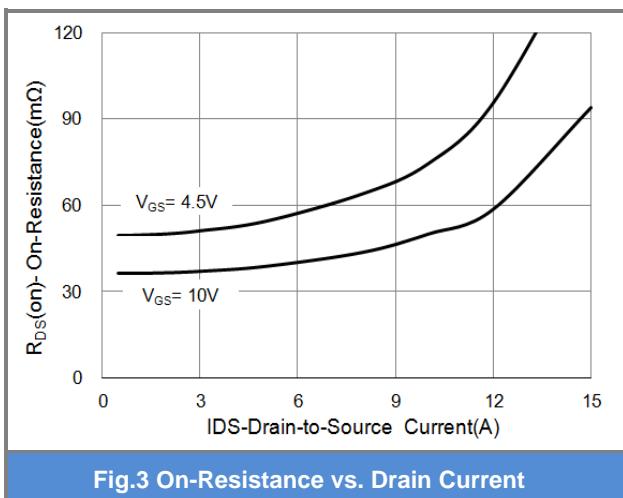


Fig.3 On-Resistance vs. Drain Current

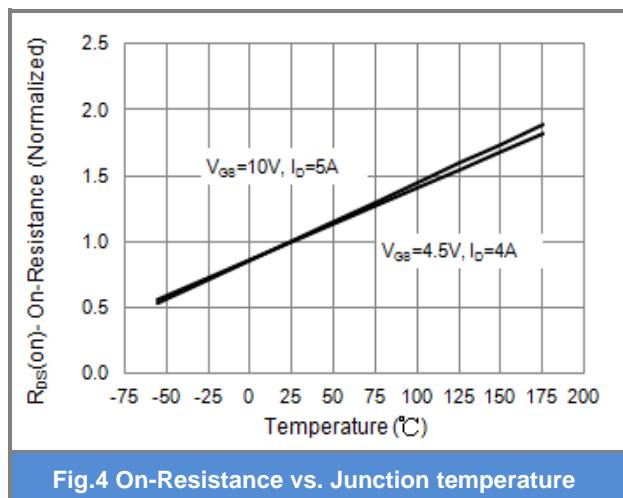


Fig.4 On-Resistance vs. Junction temperature

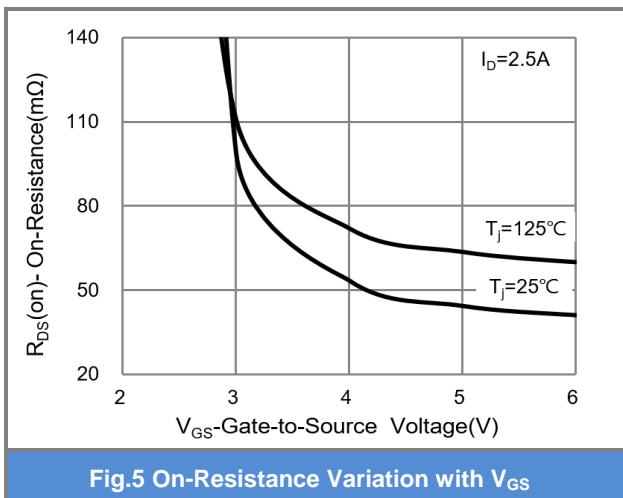


Fig.5 On-Resistance Variation with V_{GS}

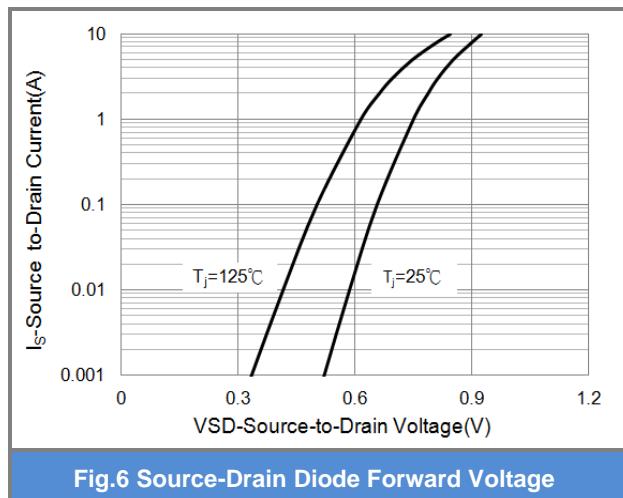


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

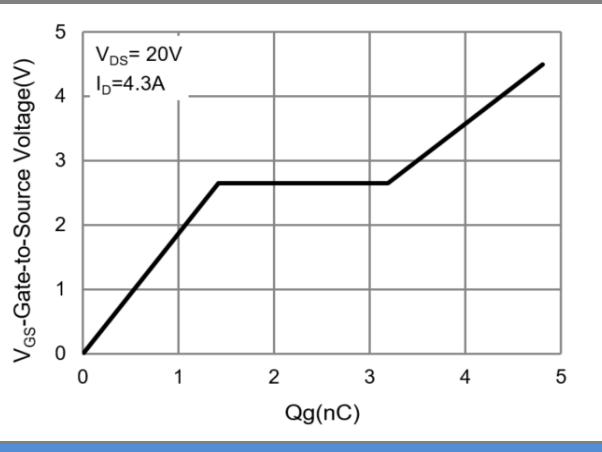


Fig.7 Gate-Charge Characteristics

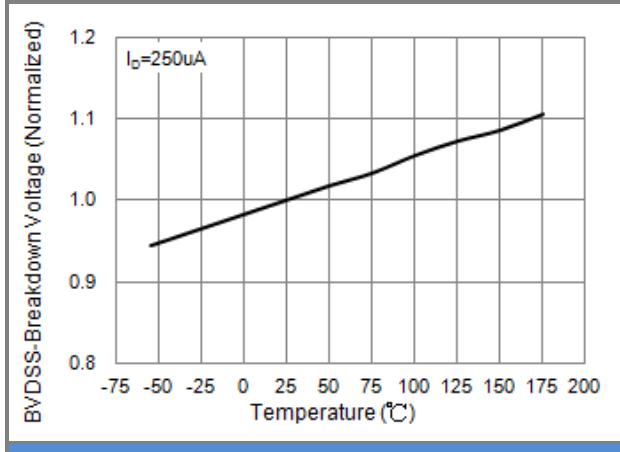


Fig.8 Breakdown Voltage Variation vs. Temperature

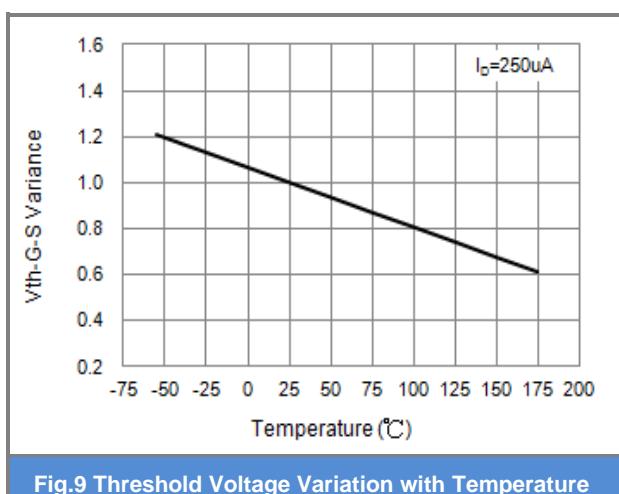


Fig.9 Threshold Voltage Variation with Temperature

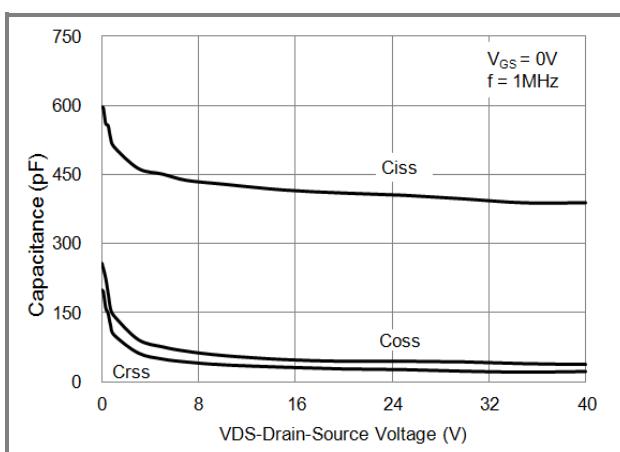


Fig.10 Capacitance vs. Drain-Source Voltage

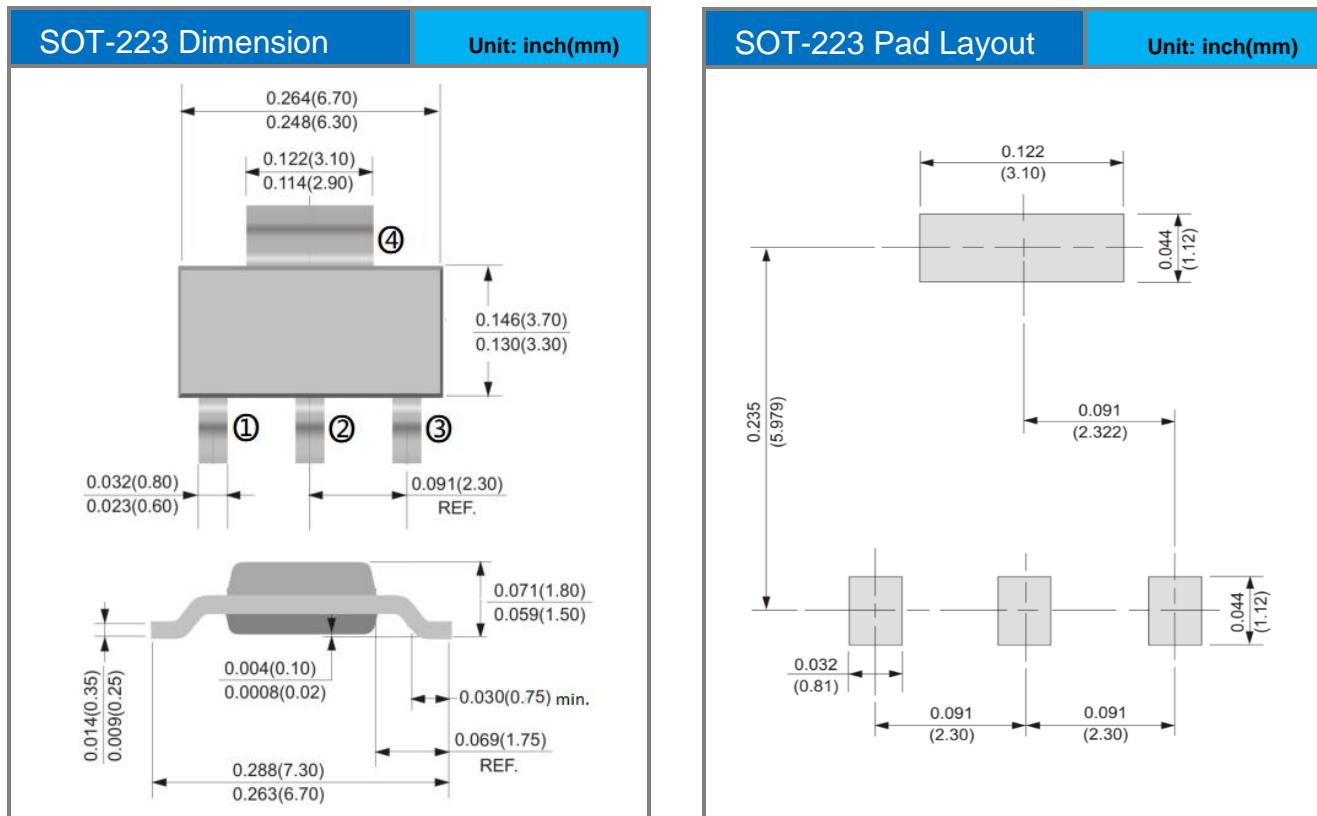


PJW7N04-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJW7N04-AU_R2_000A1	SOT-223	2,500pcs / 13" reel	W7N04	Halogen free

Packaging Information & Mounting Pad Layout





PJW7N04-AU

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